BLF7G27L-75P; BLF7G27LS-75P

Power LDMOS transistor

Rev. 2 — 14 July 2010 Product data sheet

1. Product profile

1.1 General description

75 W LDMOS power transistor for base station applications at frequencies from 2300 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f (MHz)	I_{Dq} (mA)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	$ACPR_{885k}$ (dBc)
IS-95	2300 to 2400	650	28	12	17	26	–46[1]

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

1.2 Features and benefits

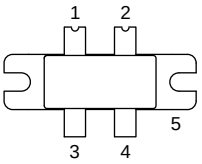
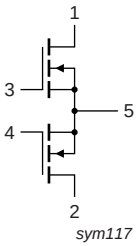
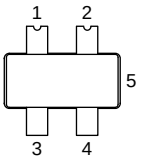
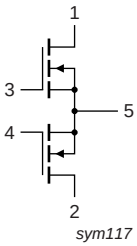
- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation (2300 MHz to 2700 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2300 MHz to 2700 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF7G27L-75P (SOT1121A)				
1	drain1			
2	drain2			
3	gate1			
4	gate2			
5	source	[1]		
BLF7G27LS-75P (SOT1121B)				
1	drain1			
2	drain2			
3	gate1			
4	gate2			
5	source	[1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF7G27L-75P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A
BLF7G27LS-75P	-	earless flanged LDMOST ceramic package; 4 leads	SOT1121B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
I_D	drain current		-	18	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	225	°C

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 10 W	0.5	K/W

6. Characteristics

Table 6. Characteristics

T_j = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.5 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 50 mA	1.3	1.8	2.3	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	5	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	9.5	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	500	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 2.5 A	-	3.8	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 3.5 A	-	0.29	-	Ω

7. Test information

Table 7. Functional test information

Mode of operation: 1-carrier N-CDMA, single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz; f_1 = 2300 MHz; f_2 = 2400 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 650 mA; T_{case} = 25 °C; 2 sections combined unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	12	-	W
G_p	power gain	$P_{L(AV)}$ = 12 W	15.8	17	-	dB
RL_{in}	input return loss	$P_{L(AV)}$ = 12 W	-	–12	–8	dB
η_D	drain efficiency	$P_{L(AV)}$ = 12 W	23	26	-	%
$ACPR_{885k}$	adjacent channel power ratio (885 kHz)	$P_{L(AV)}$ = 12 W	-	–46	–42	dBc

7.1 Ruggedness in class-AB operation

The BLF7G27L-75P and BLF7G27LS-75P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 650 mA; P_L = 75 W (CW); f = 2300 MHz.

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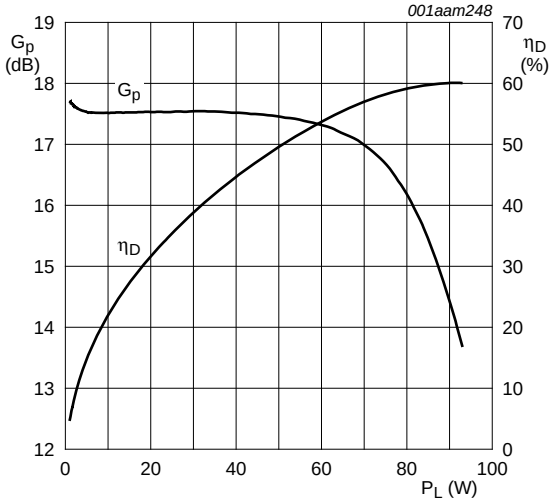
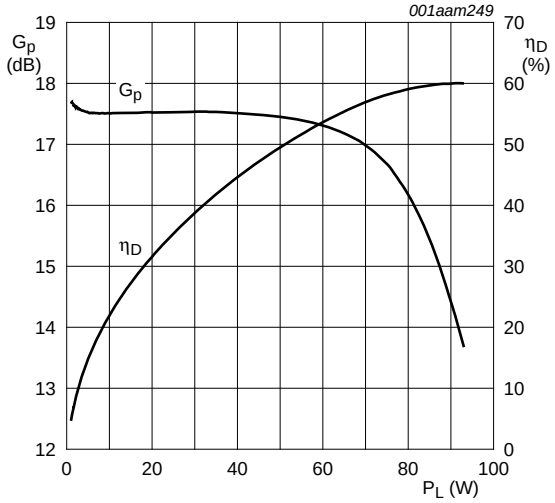
7.2 One-tone CW



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 1. One-tone CW power gain and drain efficiency as function of load power; typical values

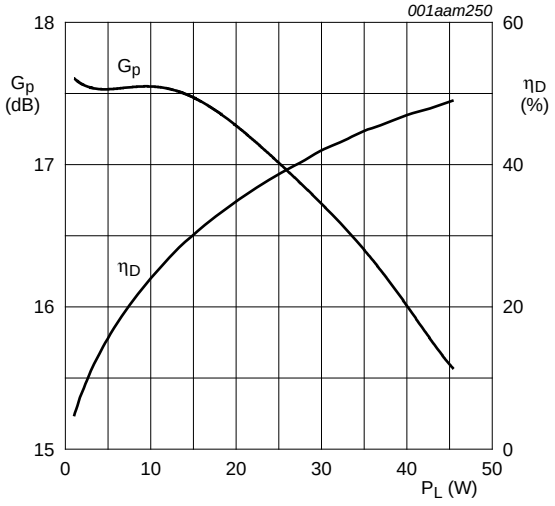


V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 2. One-tone CW power gain and drain efficiency as function of load power; typical values

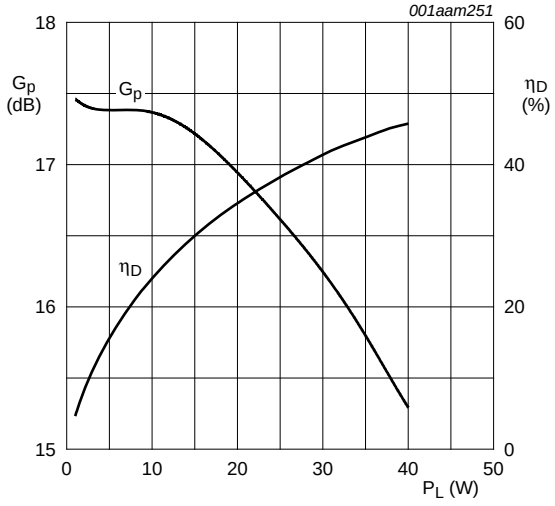
7.3 Single carrier IS-95

Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 3. Single carrier IS-95 power gain and drain efficiency as function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 4. Single carrier IS-95 power gain and drain efficiency as function of load power; typical values

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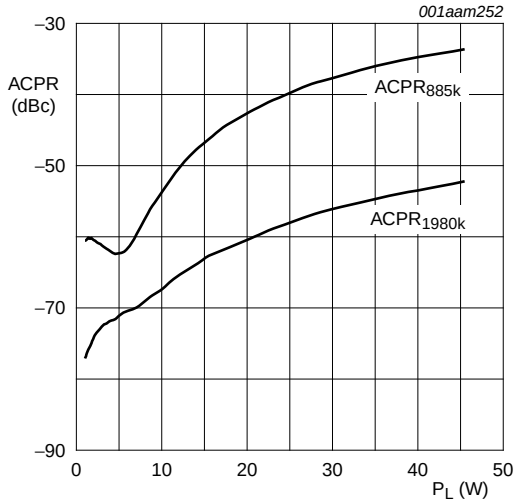
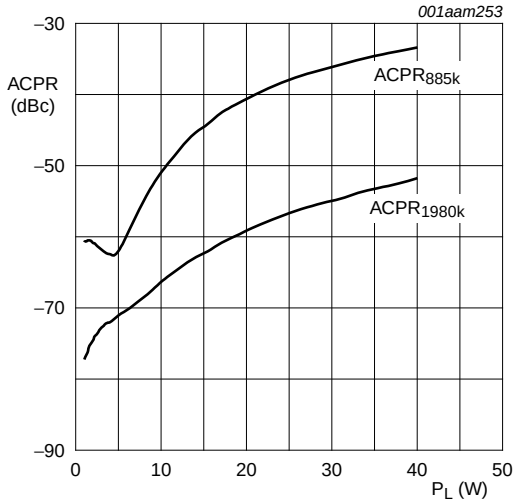


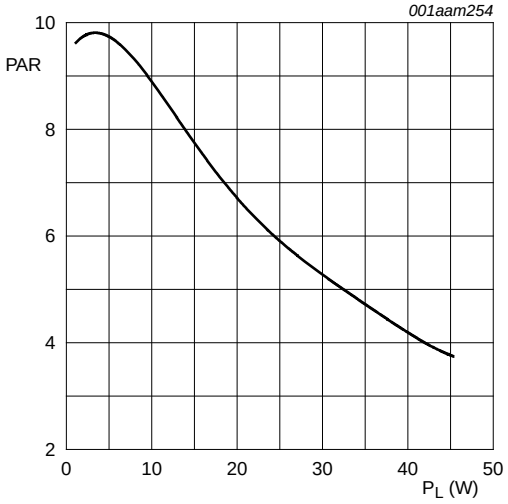
V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 5. Single carrier IS-95 ACPR at 885 kHz and at 1980 kHz as function of load power; typical values



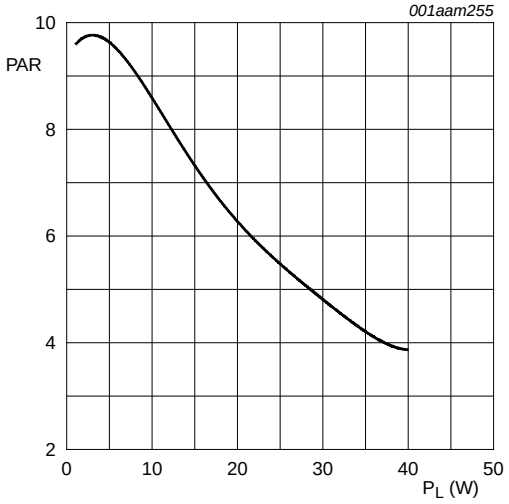
V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 6. Single carrier IS-95 ACPR at 885 kHz and at 1980 kHz as function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 7. Single carrier IS-95 peak-to-average power ratio as a function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 8. Single carrier IS-95 peak-to-average power ratio as a function of load power; typical values

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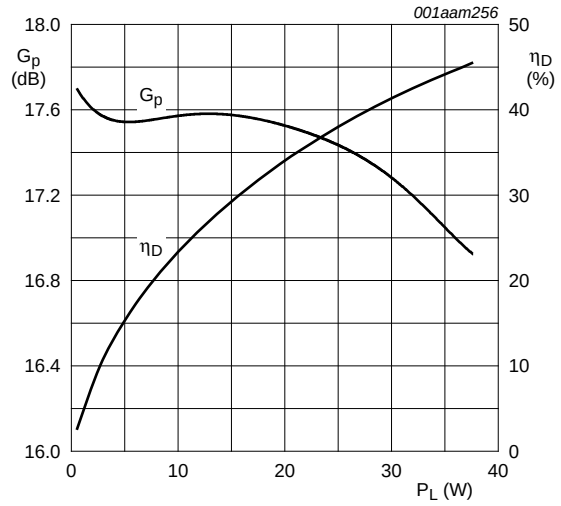
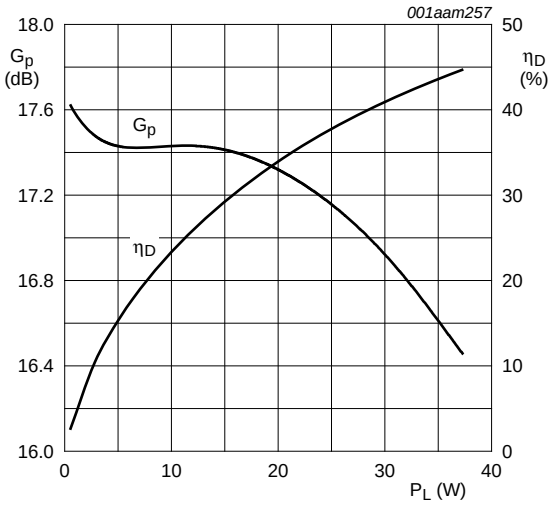
7.4 Single carrier W-CDMA

3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.



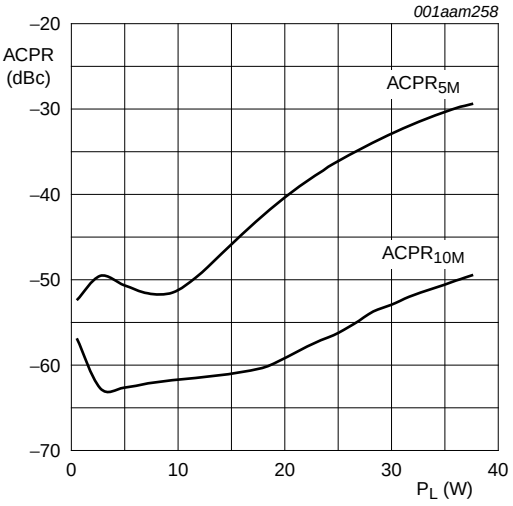
V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 9. Single carrier W-CDMA power gain and drain efficiency as function of load power; typical values



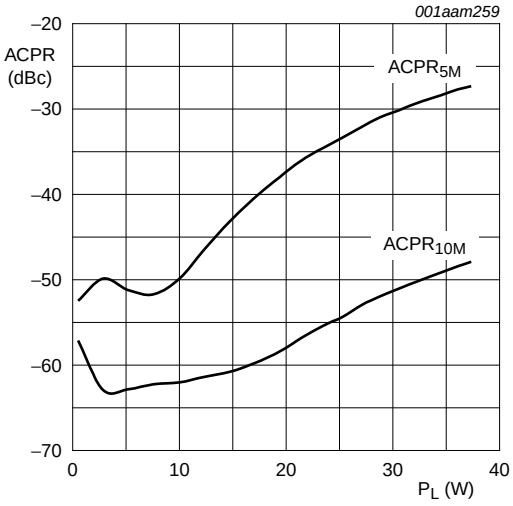
V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 10. Single carrier W-CDMA power gain and drain efficiency as function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 11. Single carrier W-CDMA ACPR at 5 MHz and at 10 MHz as function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 12. Single carrier W-CDMA ACPR at 5 MHz and at 10 MHz as function of load power; typical values

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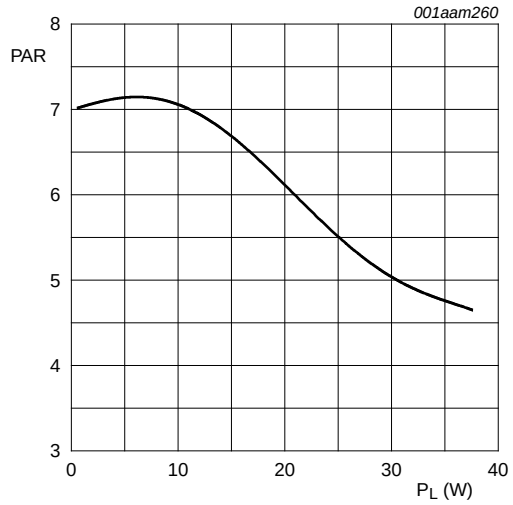
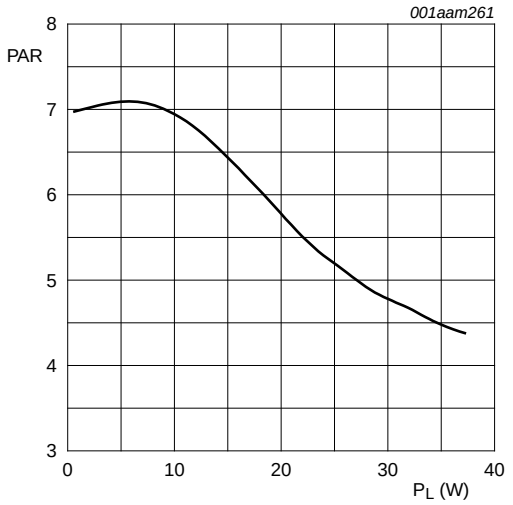


V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2300 MHz.

Fig 13. Single carrier W-CDMA peak-to-average power ratio as a function of load power; typical values



V_{DS} = 28 V; I_{Dq} = 650 mA; f = 2400 MHz.

Fig 14. Single carrier W-CDMA peak-to-average power ratio as a function of load power; typical values

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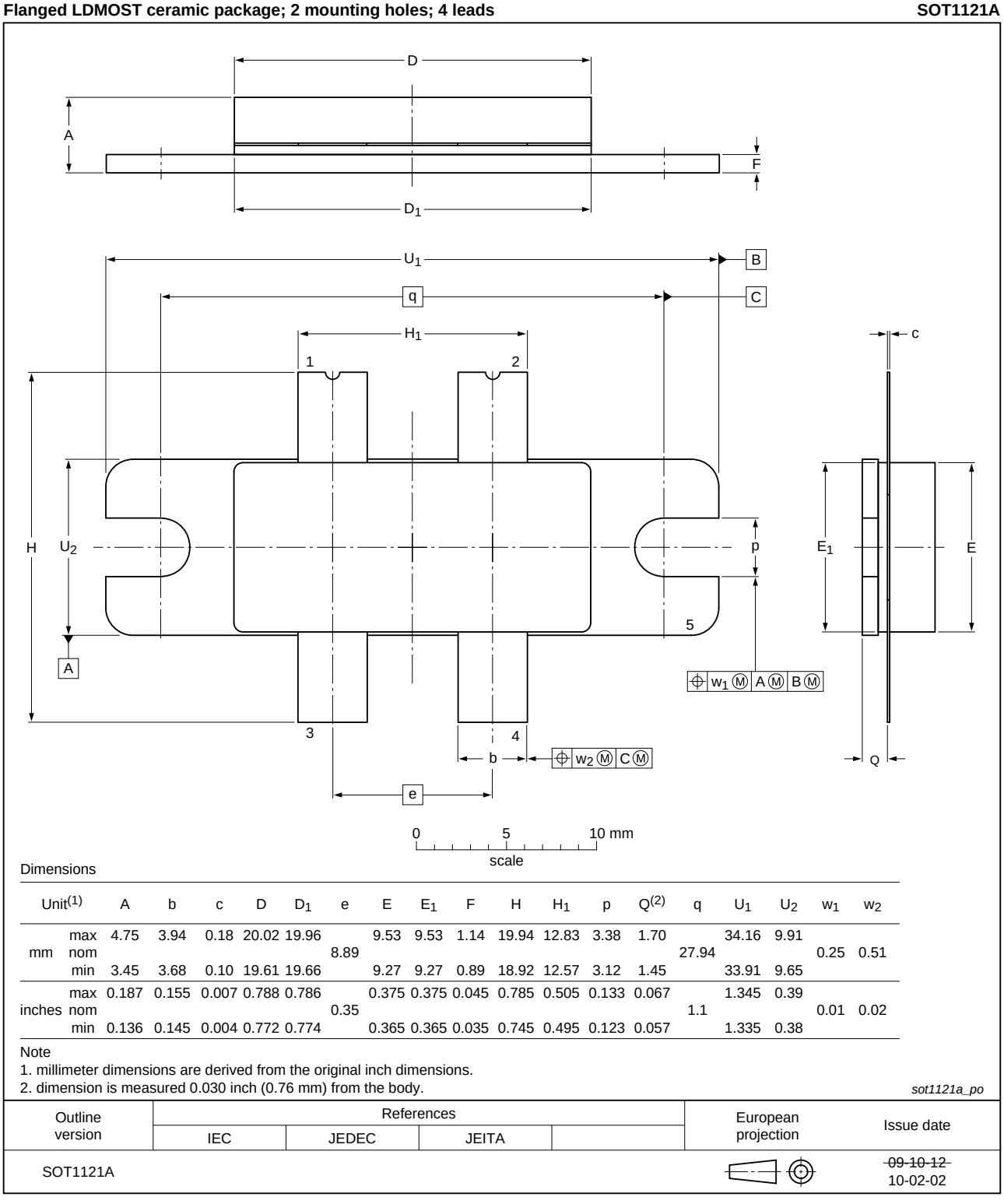
8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 4 leads **SOT1121A**



Dimensions

Unit[1]		A	b	c	D	D1	e	E	E1	F	H	H1	p	Q[2]	q	U1	U2	w1	w2
mm	max	4.75	3.94	0.18	20.02	19.96		9.53	9.53	1.14	19.94	12.83	3.38	1.70		34.16	9.91		
	nom						8.89								27.94			0.25	0.51
	min	3.45	3.68	0.10	19.61	19.66		9.27	9.27	0.89	18.92	12.57	3.12	1.45		33.91	9.65		
inches	max	0.187	0.155	0.007	0.788	0.786		0.375	0.375	0.045	0.785	0.505	0.133	0.067		1.345	0.39		
	nom						0.35								1.1			0.01	0.02
	min	0.136	0.145	0.004	0.772	0.774		0.365	0.365	0.035	0.745	0.495	0.123	0.057		1.335	0.38		

Note
1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

sot1121a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1121A						~~09-10-12~~ 10-02-02

Fig 15. Package outline SOT1121A

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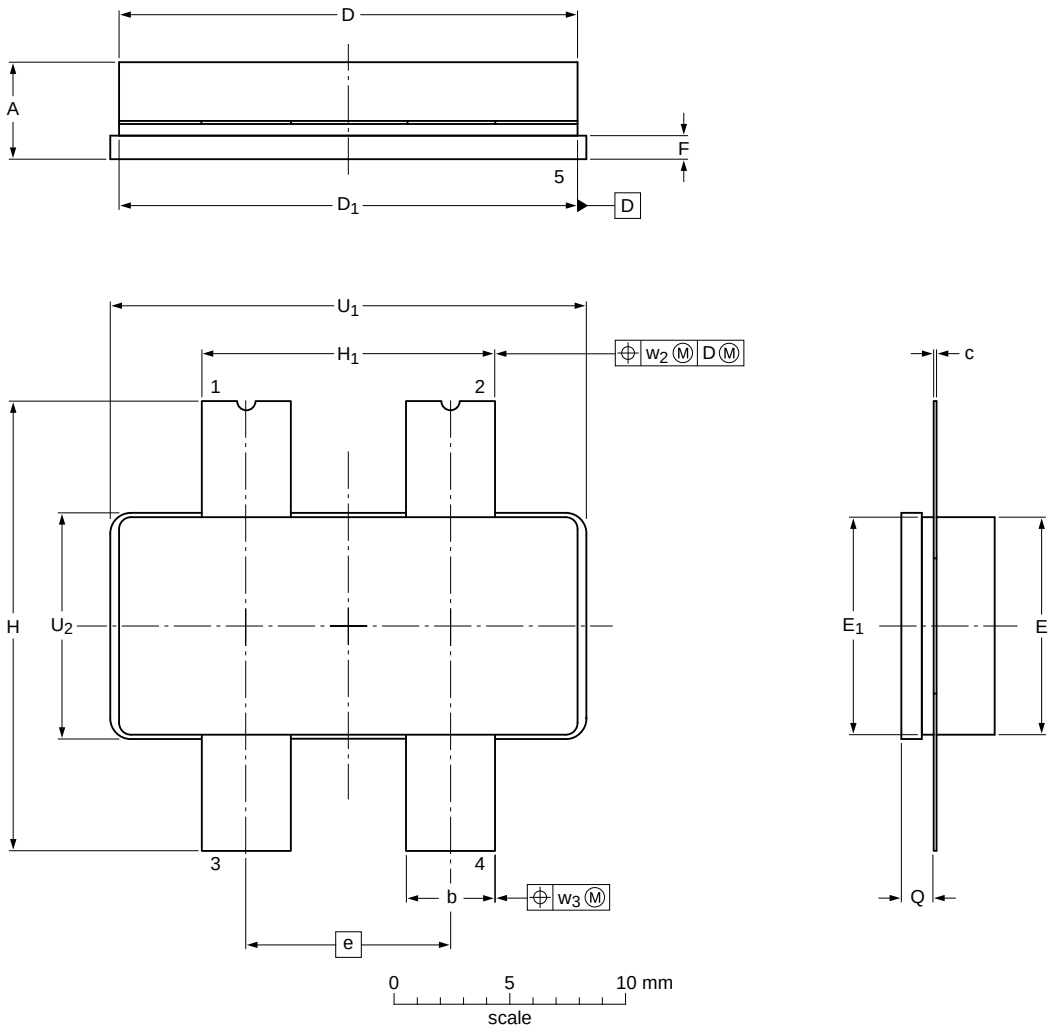
Earless flanged LDMOST ceramic package; 4 leads **SOT1121B**



Dimensions

Unit[1]		A	b	c	D	D_1	e	E	E_1	F	H	H_1	Q	U_1	U_2	w_2	w_3
mm	max	4.75	3.94	0.18	20.02	19.96		9.53	9.53	1.14	19.94	12.83	1.70	20.70	9.91		
	nom						8.89									0.51	0.25
	min	3.45	3.68	0.08	19.61	19.66		9.27	9.27	0.89	18.92	12.57	1.45	20.45	9.65		
inches	max	0.187	0.155	0.007	0.788	0.786		0.375	0.375	0.045	0.785	0.505	0.067	0.815	0.39		
	nom						0.35									0.02	0.01
	min	0.136	0.145	0.003	0.772	0.774		0.365	0.365	0.035	0.745	0.495	0.057	0.805	0.38		

Note
1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

sot1121b_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1121B						~~09-10-12~~ 09-12-14

Fig 16. Package outline SOT1121B

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9. Abbreviations

Table 8. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
3GPP	3rd Generation Partnership Project
IS-95	Interim Standard 95
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
N-CDMA	Narrowband Code Division Multiple Access
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G27L-75P_BLF7G27LS-75P v.2	20100714	Product data sheet	-	BLF7G27L-75P_ BLF7G27LS-75P v.1
Modifications:	• The status of this document has been changed to “Preliminary data sheet”. • Table 1 on page 1: changed the value of $ACPR_{885k}$ to –46 dBc. • Table 4 on page 2: added the maximum value of I_D. • Table 5 on page 3: changed several values. • Table 6 on page 3: changed several values. • Table 7 on page 3: changed several values. • Section 7.1 on page 3: changed the value of P_L. • Added Section 7.2 on page 4. • Added Section 7.3 on page 4. • Added Section 7.4 on page 6.			
BLF7G27L-75P_BLF7G27LS-75P v.1	20100329	Objective data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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